WHAT IS CLAIMED IS:

1. A composition for sealing a semiconductor device having thermoplastic properties and a line expansion coefficient of 6.0×10^{-5}[1/℃] or less at a temperature of 80℃ to 130℃.

2. A composition for sealing a semiconductor device according to claim 1, wherein the line expansion coefficient 4.75×10^{-5} [1/℃] or less at a temperature of 150℃ to 200℃.

3. A composition for sealing a semiconductor device according to claim 1, wherein a line expansion coefficient ratio between a flow direction and a normal direction of the flow direction is 0.55 or more.

4. A composition for sealing a semiconductor device according to claim 1, wherein the composition has a bending strength after solidification is 74 MPa or more.

5. A composition for sealing a semiconductor device according to claim 1, wherein an adhesion imparting agent is added to improve adhesion properties to another material by binding with a polar group.

6. A composition for sealing a semiconductor device according to claim 1, further containing silica particles.

7. A composition for sealing a semiconductor device according to claim 1, further containing a fibrous material.

8. A composition for sealing a semiconductor device according to claim 1, further containing a thermosetting resin material.

9. A composition for sealing a semiconductor device according to claim 1, wherein a product obtained by multiplying a value of a line expansion at 25 to 80℃ plus a line expansion at 80-125℃ after solidification, by a bending strength is 25 MPa or less.

10. A semiconductor device comprising:

a semiconductor element;

a semiconductor resin composition for sealing the semiconductor element; and

a conducting material electrically connected to the semiconductor element one end of which is sealed with the semiconductor resin composition,

wherein the semiconductor sealing resin composition has thermoplastic properties and a thermal expansion coefficient is 6.0×10^{-5}[1/℃] or less at a temperature of 80 to 130℃.

11. A semiconductor device according to claim 10,

wherein the semiconductor sealing resin composition has thermoplastic properties and a thermal expansion coefficient at 150 to 200℃ is 4.75×10^{-5}[1/℃] or less.

12. A semiconductor device according to claim 10,

wherein the semiconductor sealing resin composition has thermoplastic properties and a line expansion

coefficient ratio between a flow direction and a normal direction of the flow direction is 0.55 or more.

13. A semiconductor device according to claim 10, wherein a bending strength of the semiconductor sealing resin composition after solidification is 74 MPa or more.

14. A semiconductor device according to claim 10, wherein an adhesion imparting agent is added the semiconductor sealing resin composition to improve adhesion properties to another material by binding with a polar group.

15. A semiconductor device according to claim 10, wherein the semiconductor sealing resin composition contains silica particles.

16. A semiconductor device according to claim 10, wherein the semiconductor sealing resin composition contains a fibrous material.

17. A semiconductor device according to claim 10, wherein the semiconductor sealing resin composition contains a thermosetting material.

18. A semiconductor device according to claim 10, wherein the semiconductor element is coated with polyimide.

19. A semiconductor device according to claims 10 to 13, wherein the semiconductor sealing resin composition is thermoplastic and a product obtained by multiplying a value of a line expansion at 25 to 80℃

plus a line expansion at 80-125℃ after solidification, by a bending strength is 25 MPa or less.

20. A method of manufacturing a semiconductor device comprising the steps of:

electrically connecting a semiconductor element and a conducting material; and

sealing the semiconductor element with a thermoplastic semiconductor sealing resin composition and a line expansion coefficient at 80 to 130℃ is 6.0×10^{-5} [1/℃] or less.